











TPD4E001-Q1

SLLSEG0F - MARCH 2013 - REVISED SEPTEMBER 2017

# TPD4E001-Q1 4-Channel ESD Protection Array With 1.5-pF I/O Capacitance

### **Features**

- AEC-Q100 Qualified With the Following Results:
  - Device Temperature Grade 1: –40°C to 125°C Ambient Operating Temperature Range
  - Device HBM ESD Classification Level 3B
  - HBM Level 15 kV
  - Device CDM ESD Classification Level C5
- IEC 61000-4-2 Level 4 ESD Protection
  - ±8-kV Contact Discharge
  - ±15-kV Air-Gap Discharge
- IEC 61000-4-5 Surge Protection
  - 5.5 A (8/20 µs)
- Low 1.5-pF Input Capacitance
- Low 10-nA Maximum Leakage Current
- 0.9-V to 5.5-V Supply Voltage Range

## **Applications**

- **End Equipment** 
  - Automotive Head Unit
  - **Automotive Rear Seat Entertainment**
  - Automotive Rear Camera Systems
- Interfaces
  - **USB 2.0**
  - Ethernet
  - **Precision Analog Interfaces**

## 3 Description

The TPD4E001-Q1 device is a low-capacitance TVS diode array designed for ESD protection in sensitive electronics connected to communication lines. Each channel consists of a pair of transient-voltagesuppression diodes that steer ESD pulses to V<sub>CC</sub> or GND. The TPD4E001-Q1 protects against ESD events up to ±8-kV contact discharge and ±15-kV airgap discharge, as specified in IEC 61000-4-2 international standard. This device has a low capacitance of 1.5-pF per channel making it ideal for use in high-speed data interfaces. The low leakage current (10 nA maximum) ensures minimum power consumption for the system and high accuracy for analog interfaces.

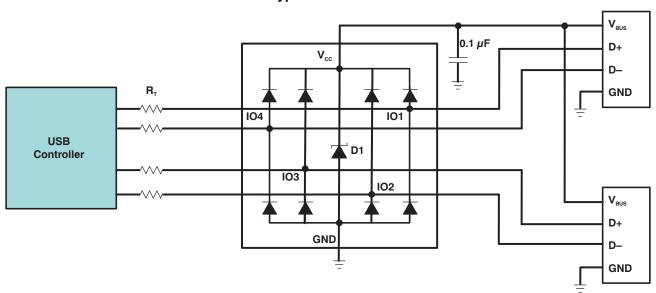
Additionally, this device is ideal for protecting automotive head units, automotive rear seat entertainment, and automotive rear camera systems that use USB 2.0, Ethernet, or precision analog interfaces.

#### Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TPD4E001-Q1	SOT-23 (6)	2.90 mm × 1.60 mm

(1) For all available packages, see the orderable addendum at the end of the datasheet.

#### **Typical Schematic**





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#### Changes from Revision C (June 2013) to Revision D

Page

- Added Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Device Functional
  Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device
  and Documentation Support section, and Mechanical, Packaging, and Orderable Information section

### Changes from Revision B (February 2012) to Revision C

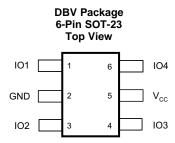
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### Changes from Revision A (April 2013) to Revision B

Page



# 5 Pin Configuration and Functions



**Pin Functions** 

	PIN	TYPE	DESCRIPTION				
NAME	NO.	ITPE	DESCRIPTION				
GND	2	GND	Ground				
IO1	1						
IO2	3	1/0					
IO3	4	I/O	ESD-protected channel				
IO4	6						
V <sub>CC</sub>	5	I	Power-supply input. Bypass V <sub>CC</sub> to GND with a 0.1-μF ceramic capacitor				

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## 6 Specifications

## 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

		MIN	MAX	UNIT
$V_{CC}$	Supply voltage	-0.3	7	V
$V_{IO}$	I/O voltage tolerance	-0.3	$V_{CC} + 0.3$	V
$I_{PP}$	Peak pulse current (Tp = 8/20 µs) <sup>(2)</sup>		5.5	Α
P <sub>PP</sub>	Peak pulse power (Tp = $8/20 \mu s$ ) <sup>(2)</sup>		100	W
$T_A$	Free air operating temperature	-40	125	ů
$T_{J}$	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature	-65	150	°C

<sup>(1)</sup> SStresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## 6.2 ESD Ratings—AEC Specification

			VALUE	UNIT
V	Electrostatic	Human-body model (HBM), per AEC Q100-002 <sup>(1)</sup>	±15000	\/
V <sub>(ESD)</sub> discharge	Charged-device model (CDM), per AEC Q100-011	±750	V	

<sup>(1)</sup> AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

## 6.3 ESD Ratings—IEC Specification

			VALUE	UNIT
V <sub>(ESD)</sub>	Clastrostatia discharge	IEC 61000-4-2 contact discharge	±8000	\/
	Electrostatic discharge	IEC 61000-4-2 air-gap discharge	±15000	V

## 6.4 ESD Ratings—ISO Specification

			VALUE	UNIT
V <sub>(ESD)</sub>	Clastrostatic discharge	ISO 10605 (330 pF, 330 $\Omega$ ) contact discharge	±8000	V
	Electrostatic discharge	ISO 10605 (330 pF, 330 Ω) air-gap discharge	±15000	V

<sup>(2)</sup> Non-repetitive current pulse 8/20 µs exponentially decaying waveform according to IEC 61000-4-5.



## 6.5 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
T <sub>A</sub>	Free air operating temperature	-40	125	°C
V <sub>CC</sub> pin	Operating voltage	0.9	5.5	٧
IO1, IO2, IO3, IO4 pins	Operating voltage	0	V <sub>CC</sub>	٧

## 6.6 Thermal Information

		TPD4E001-Q1	
	THERMAL METRIC <sup>(1)</sup>	DBV (SOT-23)	UNIT
		6 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	202.1	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	146.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	47.1	°C/W
ΨЈТ	Junction-to-top characterization parameter	37.6	°C/W
ΨЈВ	Junction-to-board characterization parameter	46.7	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

### 6.7 Electrical Characteristics

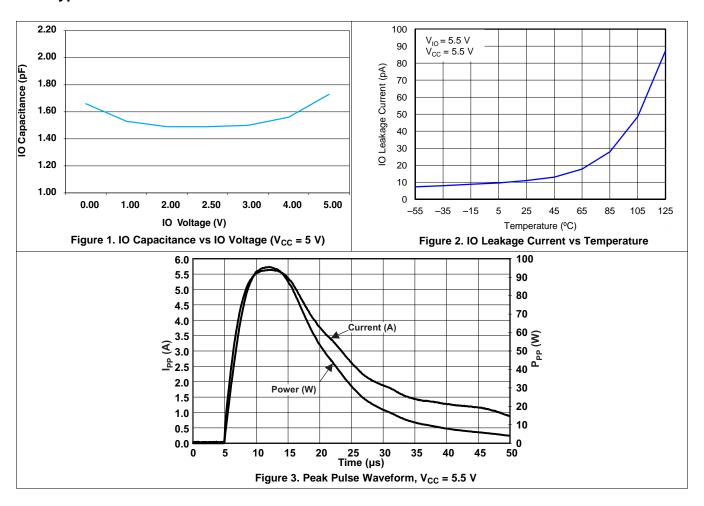
 $V_{CC} = 5 \text{ V} \pm 10\%$ , over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITION	NS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
I <sub>CC</sub>	Supply current			1	200	nA	
$V_{F}$	Diode forward voltage	I <sub>F</sub> = 10 mA	0.65		0.95	٧	
$V_{BR}$	Breakdown voltage	I <sub>BR</sub> = 10 mA	11			٧	
$V_{CLAMP}$	Clamping voltage	Surge strike $^{(2)}$ on IO pin, GND pin grounded, $V_{\rm CC} = 5.5$ V, $I_{\rm PP} = 5.5$ A	Positive transients		16		٧
$V_{RWM}$	Reverse standoff voltage	IO pin to GND pin				5.5	٧
I <sub>IO</sub>	Channel leakage current	$V_{IO}$ = GND to $V_{CC}$			±10	nΑ	
C <sub>IO</sub>	Channel input capacitance	$V_{CC} = 5 \text{ V}$ , bias of $V_{CC}/2$ , f = 10 MHz			1.5		pF

<sup>(1)</sup> Typical values are at  $V_{CC}$  = 5 V and  $T_A$  = 25°C. (2) Non-repetitive current pulse 8/20  $\mu$ s exponentially decaying waveform according to IEC 61000-4-5.



## 6.8 Typical Characteristics



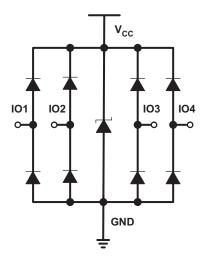


## 7 Detailed Description

#### 7.1 Overview

The TPD4E001-Q1 device is a low-capacitance, TVS diode array designed for ESD protection in sensitive electronics connected to communication lines. Each channel consists of a pair of transient voltage suppression diodes that steer ESD pulses to  $V_{CC}$  or GND. The TPD4E001-Q1 device protects against ESD events up to  $\pm 8$ -kV contact discharge and  $\pm 15$ -kV air-gap discharge, as specified in IEC 61000-4-2 international standard. This device has a low capacitance of 1.5-pF per channel making it ideal for use in high-speed data interfaces. The low-leakage current (10 nA maximum) ensures minimum power consumption for the system and high accuracy for analog interfaces.

### 7.2 Functional Block Diagram



### 7.3 Feature Description

#### 7.3.1 AEC-Q100 Qualified

This device is qualified according to the AEC-Q100 standard. The device temperature rating is Grade 1 (–40°C to +125°C). The HBM Classification Level passed is 3B (> 8 kV). The CDM Classification Level passed is C5 (all pins 750 V to <1000 V).

#### 7.3.2 IEC 61000-4-2 Level 4 ESD Protection

The device is specified at ±8-kV contact discharge and ±15-kV air gap discharge.

#### 7.3.3 IEC 61000-4-5 Surge Protection

This device is rated to pass at least 5.5-A of peak pulse current according to the IEC 61000-4-5 (8/20-µs pulse) standard.

#### 7.3.4 Low 1.5-pF Input Capacitance

This device has a typical capacitance of 1.5-pF on each of the four IO pins. This allows for high speed signals on the IO pins in excess of 1 Gbps.

#### 7.3.5 Low 10-nA (Maximum) Leakage Current

This device is rated to have a maximum leakage current of 10-nA on each of the four IO pins.

#### 7.3.6 0.9-V to 5.5-V Supply Voltage Range

This device is specified to operate with a supply voltage (on  $V_{CC}$ ) between 0.9-V and 5.5-V to ensure sufficient signal integrity.



#### 7.4 Device Functional Modes

The TPD4E001-Q1 device is a passive integrated circuit that triggers when voltages are above  $V_{BR}$  or below the lower diodes  $V_F$  (-0.6 V). During ESD events, voltages as high as  $\pm 8$  kV (contact) can be directed to ground via the internal diode network. Once the voltages on the protected line fall below the trigger levels of TPD4E001-Q1 (usually within 10s of nano-seconds) the device reverts back to its high-impedance state.

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## 8 Application and Implementation

#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 8.1 Application Information

The TPD4E001-Q1 device is a TVS diode array which is typically used to provide a path to ground for dissipating ESD events on high-speed signal lines between a human interface connector and a system. As the current from ESD passes through the TVS, only a small voltage drop is present across the diode. This is the voltage presented to the protected IC. The triggered TVS holds this voltage,  $V_{CLAMP}$ , to a safe level for the protected IC.

## 8.2 Typical Application

For this design example, one TPD4E001-Q1 device is being used in a dual USB 2.0 application. This provides a complete port protection scheme.

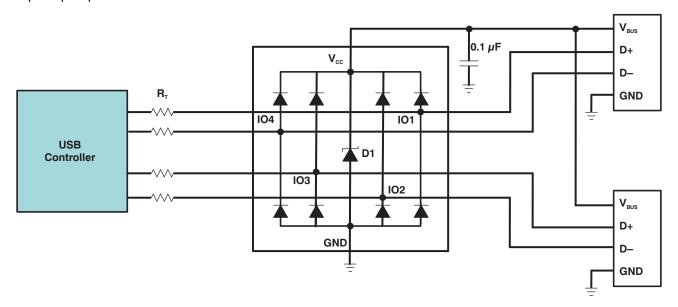


Figure 4. Typical Application Schematic

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### **Typical Application (continued)**

## 8.2.1 Design Requirements

For this design example, a single TPD4E001-Q1 device is used to protect all the pins on two USB2.0 connectors. Given the USB application, known parameters are listed in the Table 1.

**Table 1. Design Parameters** 

DESIGN PARAMETER	VALUE
Signal range on IO1, IO2, IO3, or IO4	0 V to 3.6 V
Voltage range on V <sub>CC</sub>	0 V to 5.25 V
Operating Frequency on IO1, IO2, IO3, or IO4	240 MHz

#### 8.2.2 Detailed Design Procedure

To begin the design process, some parameters must be decided upon; the designer needs to know the following:

- · Signal range on all protected lines
- · Operating frequency on all protected lines

#### 8.2.2.1 Signal Range on IO1 Through IO4

The TPD4E001-Q1 device has 4 identical protection channels for signal lines. The symmetry of the device provides flexibility when selecting which of the 4 IO channels protects which signal lines. Any IO supports a signal range of 0 to  $(V_{CC} + 0.3)$  V. Therefore, this device supports the USB 2.0 signal swing assuming  $V_{CC}$  is set appropriately.

## 8.2.2.2 Voltage Range on V<sub>CC</sub>

The V<sub>CC</sub> pin can be connected in one of two ways:

- If the  $V_{CC}$  pin connects to the system power supply, the TPD4E001-Q1 device works as a transient suppressor for any signal swing above  $V_{CC}$  +  $V_F$ . TI recommends a 0.1- $\mu F$  capacitor on the device  $V_{CC}$  pin for ESD bypass.
- If the V<sub>CC</sub> pin does not connect to the system power supply, the TPD4E001-Q1 device can tolerate higher signal swing in the range up to 10 V. Note that TI still recommends a 0.1-μF capacitor at the V<sub>CC</sub> pin for ESD bypass.

If this pin is connected to the USB 2.0  $V_{BUS}$  supply or left floating, the allowable signal swing is enough for a USB 2.0 application.

#### 8.2.2.3 Bandwidth on IO1 Through IO4

Each IO pin on the TPD4E001-Q1 device has a typical capacitance of 1.5 pF. This capacitance is low enough to easily support USB 2.0 data rates.



## 8.2.3 Application Curve

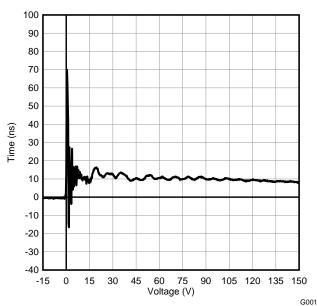


Figure 5. IEC 61000-4-2 Voltage Clamp Waveform 8-kV Contact

## 9 Power Supply Recommendations

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This device is a passive ESD protection device so there is no need to power it. Do not violate the maximum voltage specifications for each pin.



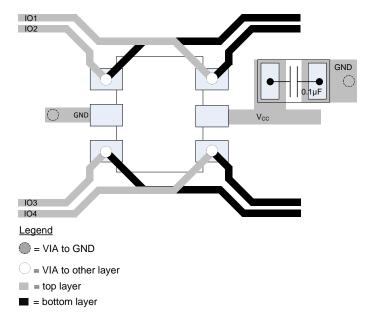
## 10 Layout

## 10.1 Layout Guidelines

When placed near the connector, the TPD4E001-Q1 device's ESD solution offers little or no signal distortion during normal operation due to low IO capacitance and ultra-low leakage-current specifications. The TPD4E001-Q1 device ensures that the core circuitry is protected and the system is functioning properly in the event of an ESD strike. For proper operation, observe the following layout and design guidelines:

- Place the TPD4E001-Q1 device solution close to the connector. This allows the device to take away the energy associated with ESD strike before it reaches the internal circuitry of the system board.
- Place a 0.1-μF capacitor very close to the V<sub>CC</sub> pin. This limits any momentary voltage surge at the IO pin during the ESD strike event.
- Ensure that there is enough metallization for the V<sub>CC</sub> and GND loop. During normal operation, the TPD4E001-Q1 device consumes nA leakage current. But during the ESD event, V<sub>CC</sub> and GND may see 15 A to 30 A of current, depending on the ESD level. Sufficient current path enables safe discharge of all the energy associated with the ESD strike.
- · Leave the unused IO pins floating.
- One can connect the V<sub>CC</sub> pin in two different ways:
  - a. If the  $V_{CC}$  pin connects to the system power supply, the TPD4E001-Q1 works as a transient suppressor for any signal swing above  $V_{CC}$  +  $V_F$ . TI recommends a 0.1- $\mu F$  capacitor on the device  $V_{CC}$  pin for ESD bypass.
  - b. If the  $V_{CC}$  pin does not connect to the system power supply, the TPD4E001-Q1 can tolerate higher signal swing in the range up to 10 V. Note that TI still recommends a 0.1- $\mu$ F capacitor at the  $V_{CC}$  pin for ESD bypass.
- The optimum placement is as close to the connector as possible.
  - EMI during an ESD event can couple from the trace being struck to other nearby unprotected traces, resulting in early system failures.
  - The PCB designer needs to minimize the possibility of EMI coupling by keeping any unprotected traces away from the protected traces which are between the TVS and the connector.
- Route the protected traces as straight as possible.
- Eliminate any sharp corners on the protected traces between the TVS and the connector by using rounded corners with the largest radii possible.
  - Electric fields tend to build up on corners, increasing EMI coupling.

#### 10.2 Layout Example



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## 11 Device and Documentation Support

## 11.1 Documentation Support

#### 11.1.1 Related Documentation

For related documentation see the following:

- Reading and Understanding an ESD Protection Datasheet
- ESD Layout Guide

### 11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

## 11.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

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**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 11.4 Trademarks

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## 11.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## 11.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

## 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



## PACKAGE OPTION ADDENDUM

23-Aug-2017

#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
TPD4E001QDBVRQ1	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	AAXQ	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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#### OTHER QUALIFIED VERSIONS OF TPD4E001-Q1:



## **PACKAGE OPTION ADDENDUM**

23-Aug-2017

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NOTE: Qualified Version Definitions:

• Catalog - TI's standard catalog product

## PACKAGE MATERIALS INFORMATION

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## TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPD4E001QDBVRQ1	SOT-23	DBV	6	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3

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#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
TPD4E001QDBVRQ1	SOT-23	DBV	6	3000	180.0	180.0	18.0	

# DBV (R-PDSO-G6)

## PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- Falls within JEDEC MO-178 Variation AB, except minimum lead width.



# DBV (R-PDSO-G6)

## PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



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